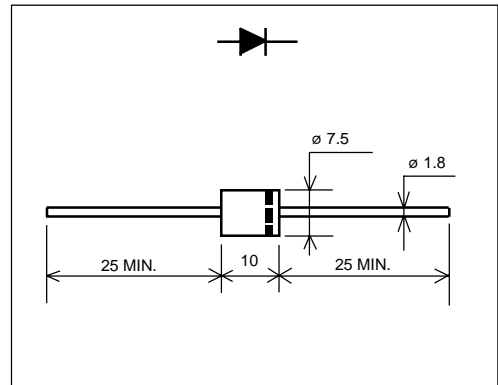


ERD29 (2.5A)

(200 to 600V / 2.5A)

FAST RECOVERY DIODE

■ Outline drawings, mm



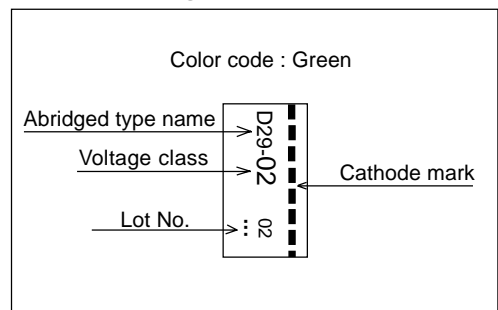
■ Features

- Large current
- High voltage by mesa design
- High reliability

■ Applications

- High speed switching

■ Marking



■ Maximum ratings and characteristics

- Absolute maximum ratings

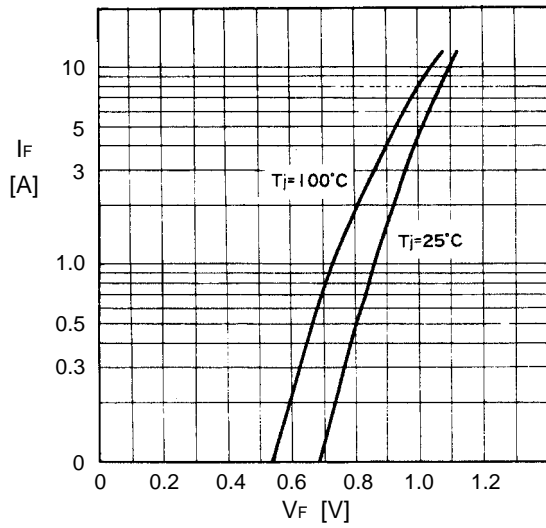
| Item | Symbol | Conditions | Rating | | | Unit |
|---------------------------------|-------------|--------------------------------------|-------------|-----|-----|-------------|
| | | | -02 | -04 | -06 | |
| Repetitive peak reverse voltage | V_{RRM} | | 200 | 400 | 600 | V |
| Average forward current | $I_{F(AV)}$ | Resistive load ($T_a=25^{\circ}C$) | 2.5 | | | A |
| Surge current | I_{FSM} | Sine wave 10ms | 70 | | | A |
| Operating junction temperature | T_j | | -30 to +125 | | | $^{\circ}C$ |
| Storage temperature | T_{stg} | | -30 to +125 | | | $^{\circ}C$ |

- Electrical characteristics ($T_a=25^{\circ}C$ Unless otherwise specified)

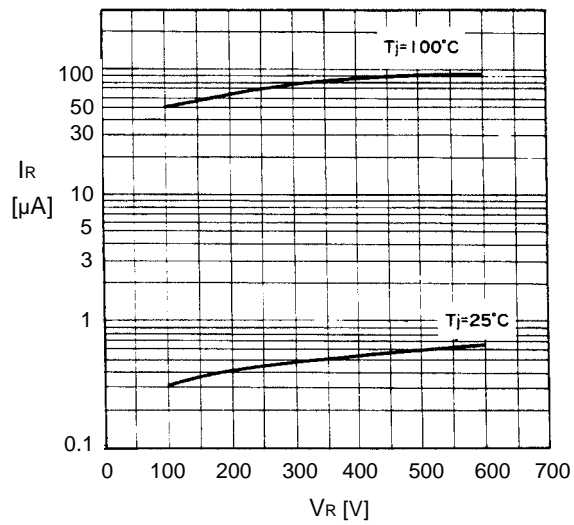
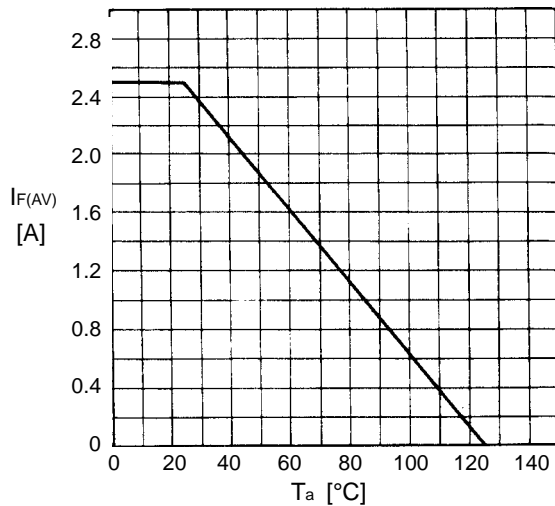
| Item | Symbol | Conditions | Max. | Unit |
|-----------------------|-----------|----------------------|------|---------|
| Forward voltage drop | V_{FM} | $I_{FM}=2.5A$ | 1.1 | V |
| Reverse current | I_{RRM} | $V_R=V_{RRM}$ | 10 | μA |
| Reverse recovery time | t_{rr} | $I_F=0.1A, I_R=0.1A$ | 0.4 | μs |

■ Characteristics

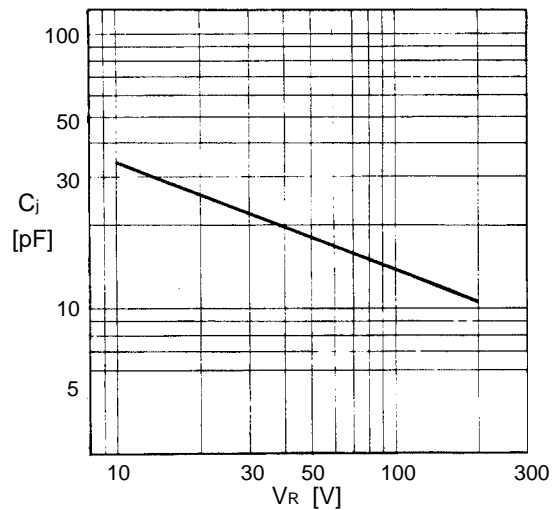
Forward characteristics



Reverse characteristics

Current derating ($I_{F(AV)}-T_a$)

Junction capacitance characteristics



Surge capability

